

## Claims

1. In a manufacturing method of a light emitting element which has an anode, a cathode, a light emitting layer which is disposed between said anode and said cathode, and a hole injection layer which is disposed between said anode and said cathode, a  
5 manufacturing method of a light emitting element characterized in that said hole injection layer is formed by phthalocyanine, and exposed to gas atmosphere after film formation of the hole injection layer.

2. A manufacturing method of a light emitting element in Claim 1, characterized in that said phthalocyanine is copper phthalocyanine.

10 3. A manufacturing method of a light emitting element in Claim 1, characterized in that an electron acceptable compound, having such a nature that it can oxidize phthalocyanine, is doped in said hole injection layer.

4. A manufacturing method of a light emitting element in Claim 1, characterized in that said gas is electron acceptable gas.

15 5. A manufacturing method of a light emitting element in Claim 1, characterized in that said gas is oxygen gas.

6. A manufacturing method of a light emitting element in Claim 3, characterized in that said electron acceptable compound is TCNQ-F4 or V<sub>2</sub>O<sub>5</sub>.

7. In a light emitting element which has an anode, a cathode, a light emitting  
20 layer which is disposed between said anode and said cathode, and a hole injection layer which is disposed between said anode and said cathode, the light emitting element characterized in that said hole injection layer includes phthalocyanine, and an electron acceptable compound which oxidizes the phthalocyanine.

8. A light emitting element in Claim 7, characterized in that said electron  
25 acceptable compound is TCNQ-F4 or V<sub>2</sub>O<sub>5</sub>.